

Abstracts

86 GHz High Power IMPATT Negative Resistance Amplifier

M. Ando, I. Haga, K. Kanekor and N. Kanmuri. "86 GHz High Power IMPATT Negative Resistance Amplifier." 1978 MTT-S International Microwave Symposium Digest 78.1 (1978 [MWSYM]): 312-314.

Describes the development of a millimeter-wave two-stage IMPATT negative resistance amplifier, using a Si DDR IMPATT diode sealed in a ceramic package to obtain a gain of 10 dB and an output power of 18 dBm in the 86 GHz frequency range.

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